

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	2.0m Ω @10V	100A
	3.0m Ω @4.5V	

Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Application

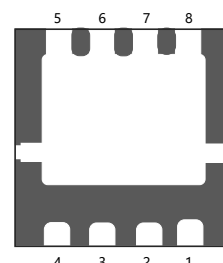
- Power Switching Application
- DC/DC Converter

MARKING:

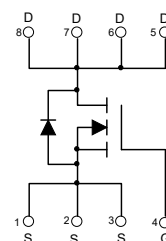


M020N03L= Device Code
 XX = Date Code
 Solid Dot = Green Indicator

PLP3.3X3.3-8L



Schematic diagram



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	30	V
Gate - Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ¹	$T_C = 25^\circ\text{C}$	I_D	100	A
	$T_C = 100^\circ\text{C}$	I_D	63	A
Pulsed Drain Current ²		I_{DM}	400	A
Single Pulsed Avalanche Current ³		I_{AS}	35	A
Single Pulsed Avalanche Energy ³		E_{AS}	306	mJ
Power Dissipation ⁵	$T_C = 25^\circ\text{C}$	P_D	63	W
Thermal Resistance from Junction to Ambient ⁶		$R_{\theta JA}$	60	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case		$R_{\theta JC}$	2	$^\circ\text{C/W}$
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~ +150	$^\circ\text{C}$

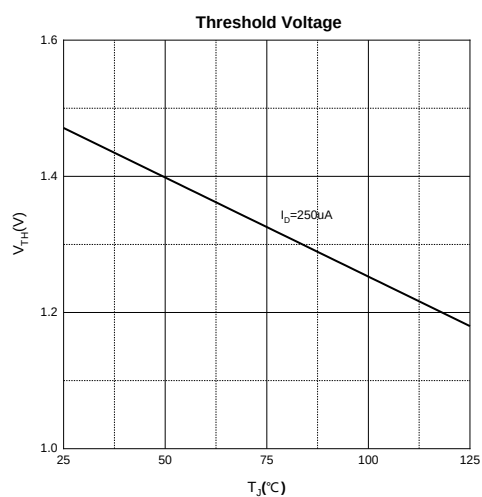
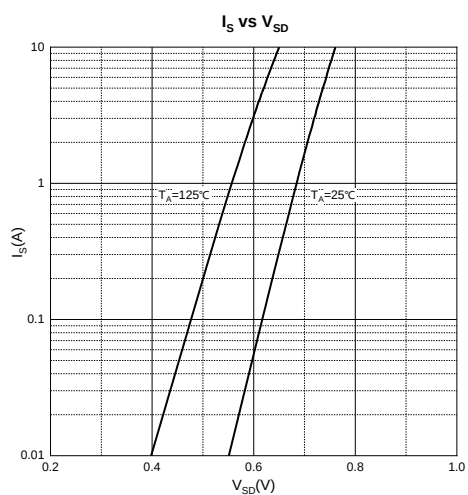
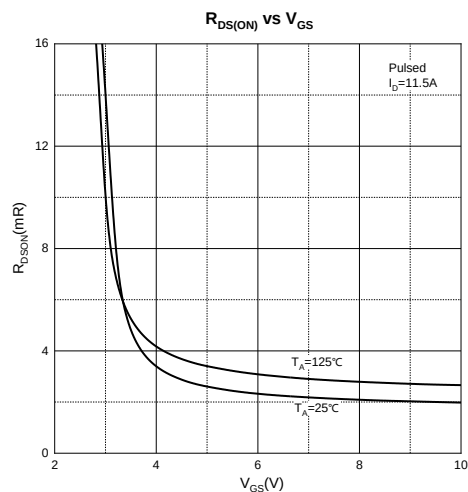
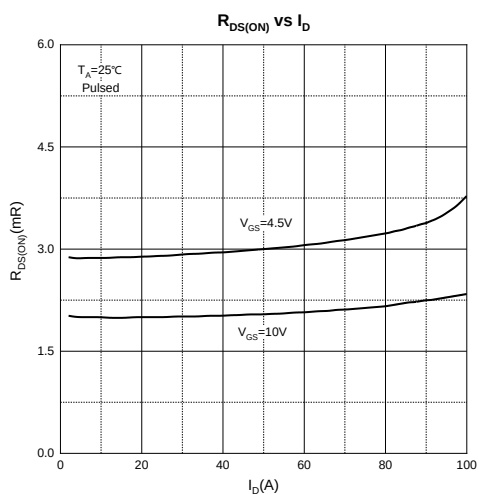
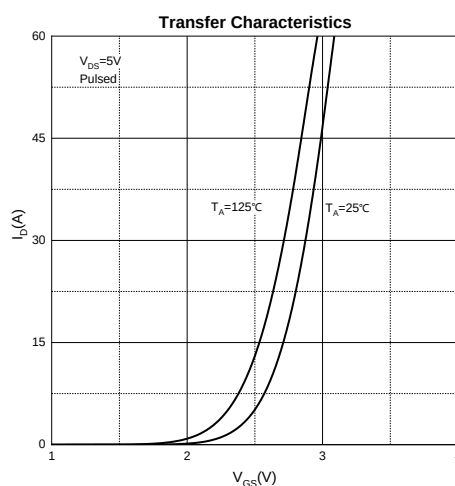
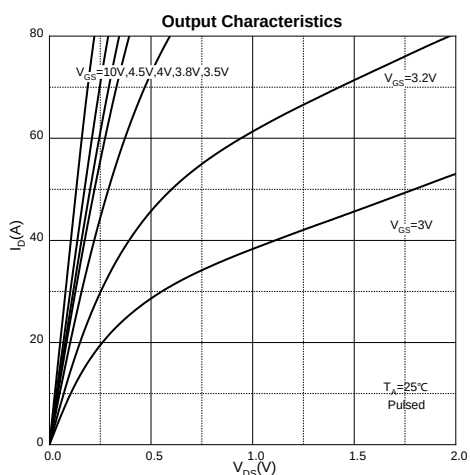
MOSFET ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

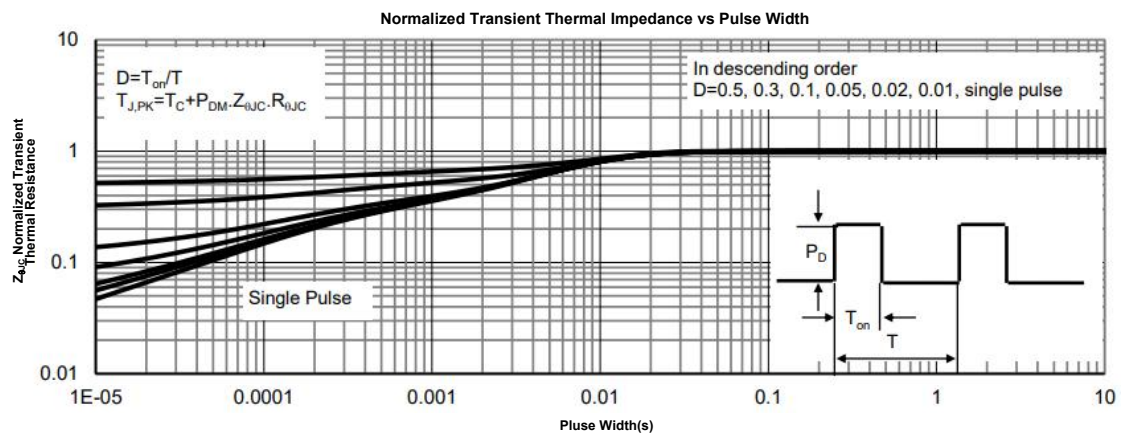
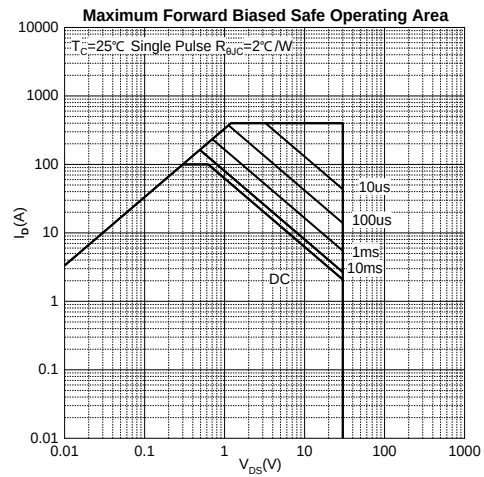
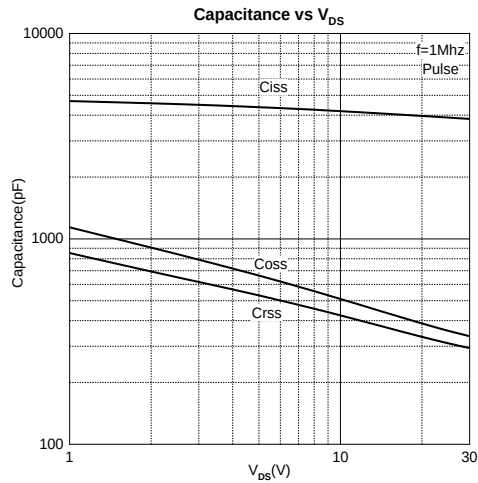
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics ⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.5	3	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$		2.0	2.6	m Ω
		$V_{GS} = 4.5V, I_D = 15A$		3.0	4.5	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$		3883		pF
Output Capacitance	C_{oss}			433		
Reverse Transfer Capacitance	C_{rss}			365		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		2.5		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 15V, V_{GS} = 10V, I_D = 15A$		77		nC
Gate-source Charge	Q_{gs}			11		
Gate-drain Charge	Q_{gd}			13		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 15V, V_{GS} = 10V, I_D = 30A,$ $R_G = 3\Omega$		14		ns
Turn-on Rise Time	t_r			27		
Turn-off Delay Time	$t_{d(off)}$			61		
Turn-off Fall Time	t_f			52		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = 10A$			1.2	V

Notes :

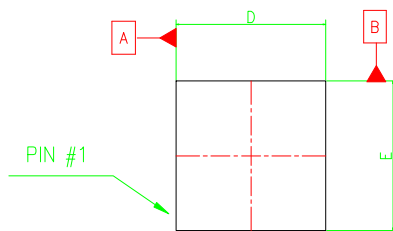
- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.EAS condition: $V_{DD} = 15V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
- 4.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 5.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.And device mounted on a large heatsink
- 6.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics

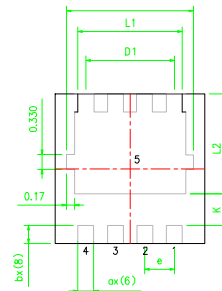




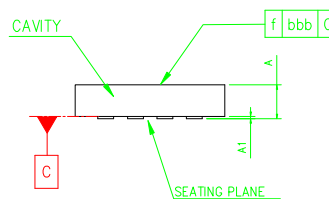
PLP3.3X3.3-8L Package Information



Top View



Bottom View



Side View

symbol	Dimension in mm		
	MIN	NOM	MAX
A	0.650	0.700	0.750
A1	0.025	0.050	0.075
D	3.200	3.300	3.400
E	3.200	3.300	3.40
D1	—	1.950	—
e	—	0.650	—
ax (6)	0.300	0.350	0.400
bx (8)	0.350	0.400	0.450
L1	2.250	2.300	2.350
L2	2.150	2.200	2.250
L3	2.750	2.800	2.850
K	0.600	0.700	0.800
bbb	0.100		
N	5		
MD/ME	4/2		